Transistors Panasonic

2SA2122

Silicon PNP epitaxial planar type

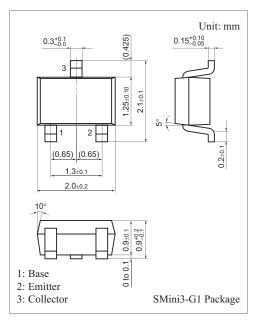
For general amplification Complementary to 2SC5950

■ Features

- High forward current transfer ratio h_{FE}
- Smini typ package, allowing downsizing of the equipment and automatic insertion through the tape packing

■ Absolute Maximum Ratings $T_a = 25$ °C

| Parameter | Symbol | Rating | Unit | |
|---------------------------------------|------------------|-------------|------|--|
| Collector-base voltage (Emitter open) | V _{CBO} | -60 | V | |
| Collector-emitter voltage (Base open) | V _{CEO} | -50 | V | |
| Emitter-base voltage (Collector open) | V_{EBO} | -7 | V | |
| Collector current | I_{C} | -100 | mA | |
| Peak collector current | I_{CP} | -200 | mA | |
| Collector power dissipation | P _C | 150 | mW | |
| Junction temperature | T _j | 150 | °C | |
| Storage temperature | T _{stg} | -55 to +150 | °C | |



Marking Symbol: 7L

■ Electrical Characteristics $T_a = 25$ °C±3°C

| Parameter | Symbol | Conditions | Min | Тур | Max | Unit |
|--|----------------------|---|-----|------|------|------|
| Collector-base voltage (Emitter open) | V_{CBO} | $I_{\rm C} = -10 \mu\text{A}, I_{\rm E} = 0$ | -60 | | | V |
| Collector-emitter voltage (Base open) | V_{CEO} | $I_{\rm C} = -2 \text{ mA}, I_{\rm B} = 0$ | -50 | | | V |
| Emitter-base voltage (Collector open) | V_{EBO} | $I_E = -10 \mu A, I_C = 0$ | -7 | | | V |
| Collector-base cutoff current (Emitter open) | I_{CBO} | $V_{CB} = -20 \text{ V}, I_E = 0$ | | | -0.1 | μΑ |
| Collector-emitter cutoff current (Base open) | I_{CEO} | $V_{CE} = -10 \text{ V}, I_{B} = 0$ | | | -100 | μΑ |
| Forward current transfer ratio | h_{FE} | $V_{CE} = -10 \text{ V}, I_{C} = -2 \text{ mA}$ | 160 | | 460 | _ |
| Collector-emitter saturation voltage | V _{CE(sat)} | $I_C = -100 \text{ mA}, I_B = -10 \text{ mA}$ | | -0.2 | -0.5 | V |
| Transition frequency | f_T | $V_{CB} = -10 \text{ V}, I_E = 1 \text{ mA}, f = 200 \text{ MHz}$ | | 80 | | MHz |
| Collector output capacitance (Common base, input open circuited) | C_{ob} | $V_{CB} = -10 \text{ V}, I_E = 0, f = 1 \text{ MHz}$ | | 2.2 | | pF |

Note) Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

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